

## **isc** Silicon NPN Power Transistor

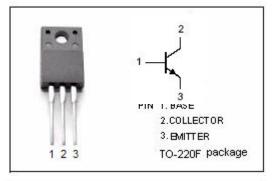
# 2SD2593

### DESCRIPTION

- Low Collector Saturation Voltage-
  - : V<sub>CE(sat)</sub>= 1.2 (Max)@ I<sub>C</sub>= 3A
- Minimum Lot-to-Lot variations for robust device
  performance and reliable operation

### APPLICATIONS

• Designed for power amplifier.



- C -

- B---+

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

ABSOLU	, <b>-S-</b> ,							
SYMBOL	PARAMETER	VALUE	UNIT	F OOO	ġ		0	¢
V <sub>CBO</sub>	Collector-Base Voltage	60	v			4	; ;- L	
V <sub>CEO</sub>	Collector-Emitter Voltage	60	v	L	-i	`→ R	<b>`</b>	
$V_{\text{EBO}}$	Emitter-Base Voltage	6	V	p				ļ
Ic	Collector Current-Continuous	3	А	N	2	m	1	
					DIM	MIN	MAX	
	Collector Current-Peak	5	А		Α	14.95	15.05	
I <sub>CM</sub>					B	10.00	10.10	1
Pc	Collector Power Dissipation @ $T_a=25^{\circ}$	2		·   /	D	4.40	4.60 0.90	8
					F	3.10	3.30	1
					H	3.70	3.90	
	Collector Power Dissipation @ T <sub>C</sub> =25℃	35	W		J	0.50	0.70	1
					Κ	13.4	13.6	1
					L	1.10	1.30	
TJ	Junction Temperature	150	°C		N	5.00	5.20	
					Q	2.70	2.90	
					R	2.20	2.40	_
T <sub>stg</sub>	Storage Temperature Range	-55~150			S	2.65	2.90	
			°C		U	6.40	6.60	



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
Vceo	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =30mA; I <sub>B</sub> = 0	60			v
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.375A			1.2	v
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 60V; I <sub>E</sub> = 0			200	μA
Iceo	Collector Cutoff Current	V <sub>CB</sub> = 30V; I <sub>E</sub> = 0			300	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> =6V; I <sub>C</sub> = 0			1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 4V	70		250	
h <sub>FE-2</sub>	DC Current Gain	Ic= 3A ; Vce= 4V	10			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A ;V <sub>CE</sub> = 10V; f=10MHz		30		MHz
ton	Turn-on Time			0.5		μs
t <sub>f</sub>	Fall Time	-		0.4		μS

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